



III-V Nitride: Materials, Physics and Devices

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Deadline for manuscript submissions:

closed (15 June 2019)

Message from the Guest Editors

During the last decades, III-V nitrides materials and their optical/electronic devices have been spectacular in many research and applications, such as light emitting diodes (LEDs), laser diodes (LDs), photodiodes, solar cells, RF transistors, and power devices. High-crystalline quality GaN, AlN, AlGaIn, InGaIn layers and their structures have been obtained. Considerable efforts have been made on the material and device physics. Especially, with the recent development of the high-quality free-standing GaN substrate with dislocation density lower than 10^5cm^{-2} , intrinsic material/device physics and high-performance optical/electronic and power devices are highly expected.

The Special Issue of the journal Applied Sciences, 'III-V Nitrides: material, physics and devices', aims to cover the recent advances in the development of III-V nitrides materials and physics properties, as well as the advanced device concepts and developments.





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Message from the Editor-in-Chief

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